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P-Channel 60-V (D-S) MOSFET

| PRODUCT SUMMARY | | | | | | | |
|---------------------|-------------------------------------|---------------------------------|-----------------------|--|--|--|--|
| V _{DS} (V) | $R_{DS(on)}(\Omega)$ | I _D (A) ^a | Q _g (Typ.) | | | | |
| - 60 | 0.0486 at V _{GS} = - 10 V | - 53 | 76 nC | | | | |
| | 0.0568 at V _{GS} = - 4.5 V | - 42 | 70110 | | | | |

FEATURES

- DT-Trench Power MOSFET
- 100 % UIS Tested



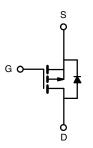
Load Switch





TO-220 Pin Configuration





P-Channel MOSFET

| ABSOLUTE MAXIMUM RATING | S (T _A = 25 °C, unle | ess otherwise not | ed) | | |
|--|--|-------------------|--------------------|----|--|
| Parameter | Symbol | Limit | Unit | | |
| Drain-Source Voltage | V _{DS} | - 60 | V | | |
| Gate-Source Voltage | V _{GS} | ± 20 | | | |
| | T _C = 25 °C | | - 53 ^a | | |
| Continuous Drain Current /T 150 °C) | T _C = 70 °C | | - 46.8 | | |
| Continuous Drain Current (T _J = 150 °C) | T _A = 25 °C | I _D | 9.2 ^b | | |
| | T _A = 70 °C | | - 8.1 ^b | A | |
| Pulsed Drain Current | | I _{DM} | - 150 | | |
| Avalanche Current Pulse | L = 0.1 mH | I _{AS} | - 45 | | |
| Single Pulse Avalanche Energy | L = 0.1 min | E _{AS} | 101 | mJ | |
| Continuous Courses Brain Binds Coursest | T _C = 25 °C | | 53 ^a | Α | |
| Continuous Source-Drain Diode Current | T _A = 25 °C | I _S | 2.1 ^b | | |
| | T _C = 25 °C | | 104.2 ^a | w | |
| Mantagara Barra Birata attan | T _C = 70 °C | В | 66.7 ^a | | |
| Maximum Power Dissipation | T _A = 25 °C | P _D | 3.1 ^b | | |
| | T _A = 70 °C | | 2 ^b | | |
| Operating Junction and Storage Temperature R | T _J , T _{stg} | - 55 to 150 | °C | | |

| THERMAL RESISTANCE RATINGS | | | | | | | |
|--|--------------|-------------------|---------|------|------|--|--|
| Parameter | Symbol | Typical | Maximum | Unit | | | |
| Maximum Junction-to-Ambient ^b | Steady State | R _{thJA} | 33 | 40 | °C/W | | |
| Maximum Junction-to-Case | Steady State | R _{thJC} | 0.98 | 1.2 | C/VV | | |

Notes:

- a. Based on T_C = 25 °C.
- b. Surface mounted on 1" x 1" FR4 board.



| Parameter | Symbol | Test Conditions | Min. | Тур. | Max. | Unit |
|---|-------------------------|---|-------|--------|--------|-------|
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$ | - 60 | | | V |
| V _{DS} Temperature Coefficient | $\Delta V_{DS}/T_{J}$ | I _D = - 250 μA | | 68 | | mV/°C |
| V _{GS(th)} Temperature Coefficient | $\Delta V_{GS(th)}/T_J$ | 1Β = - 250 μΑ | | - 5.2 | | |
| Gate-Source Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_{D} = -250 \mu A$ | - 1 | | - 3 | V |
| Gate-Source Leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | | | ± 100 | nA |
| Zara Cata Valtaga Drain Current | 1 | V _{DS} = - 60 V, V _{GS} = 0 V | | | - 1 | μΑ |
| Zero Gate Voltage Drain Current | IDSS | V _{DS} = - 60 V, V _{GS} = 0 V, T _J = 55 °C | | | - 10 | |
| On-State Drain Current ^a | I _{D(on)} | V _{DS} = - 5 V, V _{GS} = - 10 V | - 120 | | | Α |
| D : 0 | В | V _{GS} = - 10 V, I _D = - 30 A | | 0.0486 | 0.0534 | _ |
| Drain-Source On-State Resistance ^a | R _{DS(on)} | V _{GS} = - 4.5 V, I _D = - 20 A | | 0.0568 | 0.0624 | Ω |
| Forward Transconductance ^a | 9 _{fs} | V _{DS} = - 15 V, I _D = - 50 A | 20 | | | S |
| Dynamic ^b | | | | | | |
| Input Capacitance | C _{iss} | | | 3500 | | pF |
| Output Capacitance | C _{oss} | $V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$ | | 390 | | |
| Reverse Transfer Capacitance | C _{rss} | | | 290 | | |
| Total Gata Chargo | Q_g | $V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -55 \text{ A}$ | | 76 | 115 | nC |
| Total Gate Charge | | | | 38 | 60 | |
| Gate-Source Charge | Q_{gs} | $V_{DS} = -30 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -55 \text{ A}$ | | 16 | | |
| Gate-Drain Charge | Q_{gd} | | | 19 | | |
| Gate Resistance | R_g | f = 1 MHz | | 5.2 | | Ω |
| Turn-On Delay Time | t _{d(on)} | | | 10 | 15 | |
| Rise Time | t _r | $V_{DD} = -2 V$, $R_L = 2 \Omega$ | | 7 | 15 | ns |
| Turn-Off Delay Time | t _{d(off)} | $I_D \cong$ - 10 A, V_{GEN} = - 10 V, R_g = 1 Ω | | 70 | 110 | |
| Fall Time | t _f | | | 40 | 60 | |
| Drain-Source Body Diode Characteristic | s | | | | | |
| Continuous Source-Drain Diode Current | I _S | T _C = 25 °C | | | - 53 | А |
| Pulse Diode Forward Current ^a | I _{SM} | | | | - 150 | |
| Body Diode Voltage | V _{SD} | I _S = - 30 A | | - 1 | - 1.5 | V |
| Body Diode Reverse Recovery Time | t _{rr} | | | 45 | 68 | ns |
| Body Diode Reverse Recovery Charge | Q _{rr} | I _F = - 50 A, di/dt = 100 A/μs, T _{.I} = 25 °C | | 59 | 120 | nC |
| Reverse Recovery Fall Time | t _a | $ 1_F - 30 \text{ A}, \text{ u/u} = 100 \text{ A/} \mu \text{s}, 1_J = 25 \text{ C}$ | | 29 | | ns |
| Reverse Recovery Rise Time | t _b | | | 16 | | |

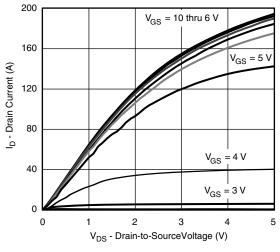
Notes:

- a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

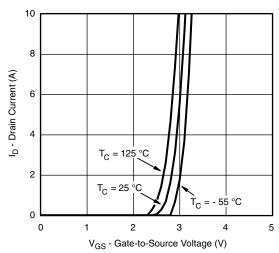
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



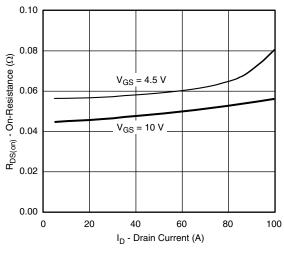
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



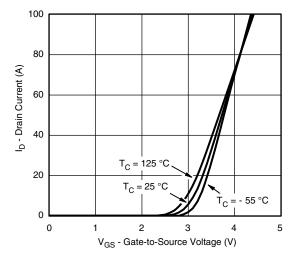
Output Characteristics



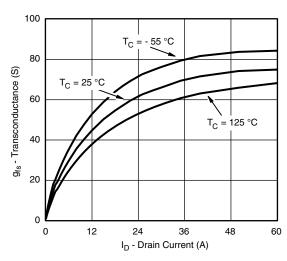
Transfer Characteristics



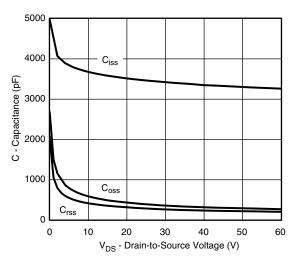
On-Resistance vs. Drain Current



Transfer Characteristics



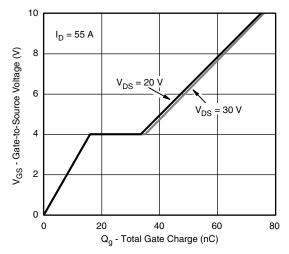
Transconductance



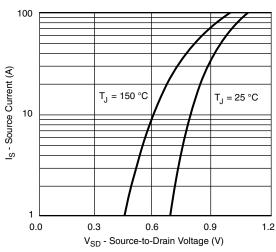
Capacitance



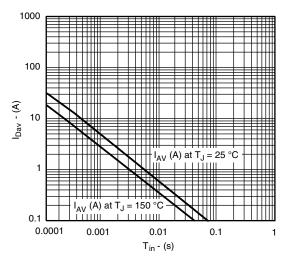
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



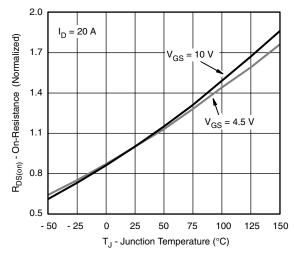
Gate Charge



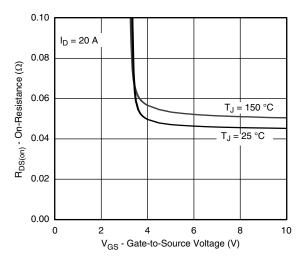
Source-Drain Diode Forward Voltage



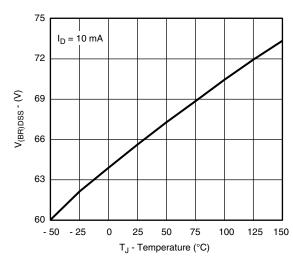
Single Pulse Avalanche Current Capability vs. Time



On-Resistance vs. Gate-to-Source Voltage



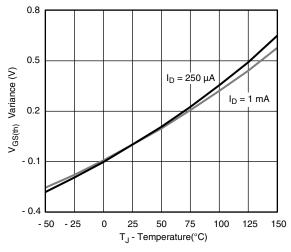
On-Resistance vs. Gate-to-Source Voltage



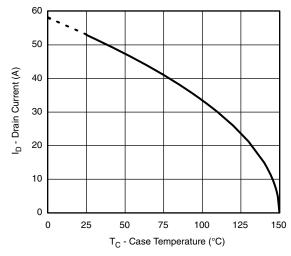
Drain-Source Breakdown Voltage vs. Junction Temperature

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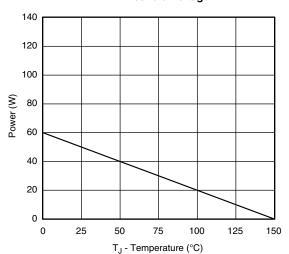
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



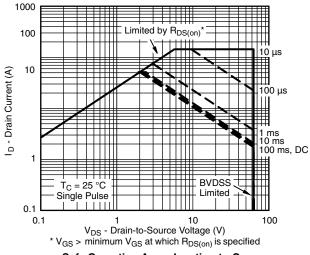
Din-Tek SEMICONDUCTOR



Threshold Voltage

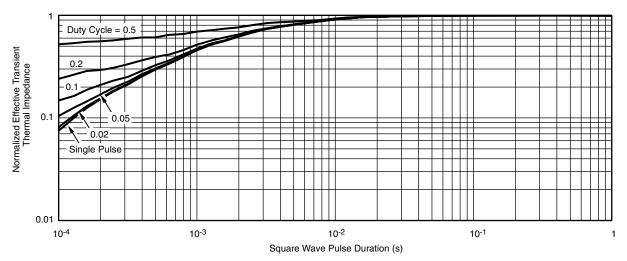


Max. Drain Current vs. Case Temperature



Power Derating, Junction-to-Case

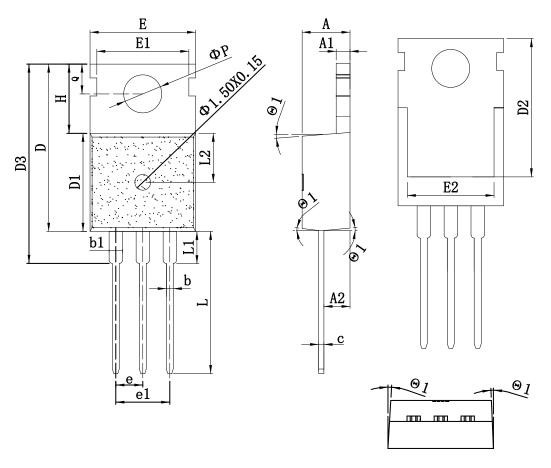




Normalized Thermal Transient Impedance, Junction-to-Case



TO-220_3L-A PACKAGE OUTLINE

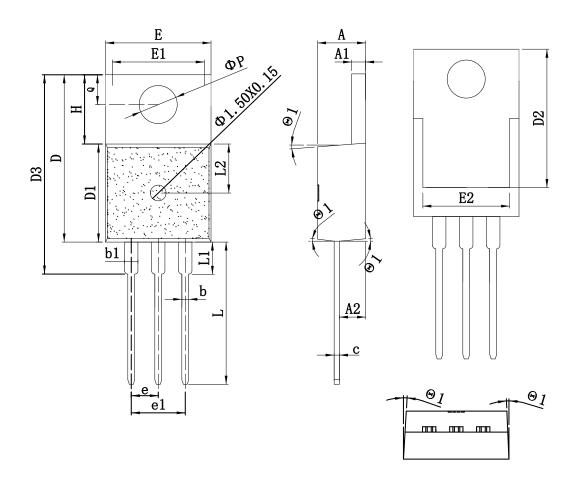


COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

| SYMBOL | mm | | | SYMBOL | mm | | | |
|---------|-------|-------|-------|--------|---------|-------|-------|--|
| STWIDOL | MIN | TYP | MAX | SIMBOL | MIN | TYP | MAX | |
| A | 4.15 | 4.50 | 4.80 | E1 | 8.25 | 8.70 | 9.15 | |
| A1 | 1.15 | 1.30 | 1.50 | E2 | 7.20 | 8.00 | 8.80 | |
| A2 | 2.10 | 2.40 | 2.65 | e | 2.38 | 2.54 | 2.74 | |
| b | 0.65 | 0.80 | 1.00 | e1 | 5.08REF | | | |
| bl | 1.10 | 1.33 | 1.80 | Н | 6.20 | 6.50 | 6.90 | |
| С | 0.35 | 0.50 | 0.65 | L | 12.75 | 13.28 | 13.70 | |
| D | 14.25 | 15.75 | 16.15 | L1 | - | - | 3.50 | |
| D1 | 8.70 | 9.20 | 9.60 | L2 | 2.30 | 4.65 | 7.00 | |
| D2 | 12.30 | 13.10 | 13.85 | φP | 3.40 | 3.65 | 3.85 | |
| D3 | 16.20 | 18.80 | 20.60 | Q | 2.50 | 2.80 | 3.00 | |
| Е | 8.68 | 10.02 | 11.00 | θ | 2° | - | 7° | |



TO-220_3L-B PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

| SYMBOL | | mm | | SYMBOL | mm | | | |
|--------|-------|-------|-------|--------|---------|-------|-------|--|
| SIMBOL | MIN | TYP | MAX | | MIN | TYP | MAX | |
| A | 4.15 | 4.50 | 4.80 | E1 | 8.25 | 8.70 | 9.15 | |
| A1 | 1.15 | 1.30 | 1.50 | E2 | 7.20 | 8.00 | 8.80 | |
| A2 | 2.10 | 2.40 | 2.65 | e | 2.38 | 2.54 | 2.74 | |
| b | 0.65 | 0.80 | 1.00 | e1 | 5.08REF | | | |
| b1 | 1.10 | 1.33 | 1.80 | Н | 6.20 | 6.50 | 6.90 | |
| c | 0.35 | 0.50 | 0.65 | L | 12.75 | 13.28 | 13.70 | |
| D | 14.25 | 15.75 | 16.15 | L1 | 1 | 1 | 3.50 | |
| D1 | 8.70 | 9.20 | 9.60 | L2 | 2.30 | 4.65 | 7.00 | |
| D2 | 12.30 | 13.10 | 13.85 | φP | 3.40 | 3.65 | 3.85 | |
| D3 | 16.20 | 18.80 | 20.60 | Q | 2.50 | 2.80 | 3.00 | |
| Е | 8.68 | 10.02 | 11.00 | θ | 2° | - | 7° | |





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